

10 输出低抖动低功率时钟缓冲器和电平转换器

查询样片: [CDCLVC1310](#)

特性

- 支持 **-169dBc/Hz** 超低本底噪声的高性能晶振缓冲器
- 附加的相位噪声/抖动性能为 **25 fs_{RMS}** (典型值)
- 具有 **3.3V** 或 **2.5V** 内核电压和 **3.3V**, **2.5V**, **1.8V** 或 **1.5V** 输出电源的电平转换
- 器件输入包括主级、次级和晶振输入并可使用输入 **MUX** 进行手工选择 (通过引脚)。主级和次级输入能够接受低电压正射极耦合逻辑 (**LVPECL**), 低压差分信号 (**LVDS**), 主机时钟信号电平 (**HCSL**), **SSTL** 或者低压 **CMOS (LVCMOS)** 信号和晶振输入。
 - 支持 **8MHz** 至 **50MHz** 的晶振频率
 - 支持高达 **200MHz** 的差分 and 单端输入频率。
- **10** 个单端 **LVC MOS** 输出。输入可运行在 **1.5V**, **1.8V**, **2.5V** 或者 **3.3V** 的电源电压下。
 - **LVC MOS** 输出运行频率高达 **200MHz**
 - 输出偏移为 **30ps** (典型值)
 - 总传播延迟为 **2ns** (典型值)
 - 同步和无毛刺脉冲输出启用可用
- 采用方形扁平无引脚 (**QFN**)-**32 5mm x 5mm** 封装, 其工业温度范围为 **-40°C** 至 **85°C**。
- 能够过度驱动 **LVC MOS** 信号高达 **50MHz** 的晶振输入

应用范围

- 无线和有线基础设施
- 网络和数据通信
- 医疗成像
- 便携式测试和测量
- 高端 **A/V**

说明

CDCLVC1310 是一款多用途、低抖动、低功率时钟扇出缓冲器, 此缓冲器可将来自 3 个输入中的 1 个分配到 10 个低抖动 **LVC MOS** 时钟输出, 这 3 个输入的主和副输入特有差分或者单端信号和晶振输入。此类缓冲器适合用于多种移动和有线基础设施、数据通信、计算、低功率医疗成像和便携式测试和测量应用。当输入为非法电平时, 此输出在一个确定的状态上。可将内核电压设定在 **2.5V** 或 **3.3V** 上, 将输出设定在 **1.5V**, **1.8V**, **2.5V** 或 **3.3V** 上。引脚编程可轻松地配置 CDCLVC1310。总体附加抖动性能为 **25fs_{RMS}** (典型值)。CDCLVC1310 封装在小型 **32 引脚 5mm x 5mm QFN** 封装内。



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

BLOCK DIAGRAM

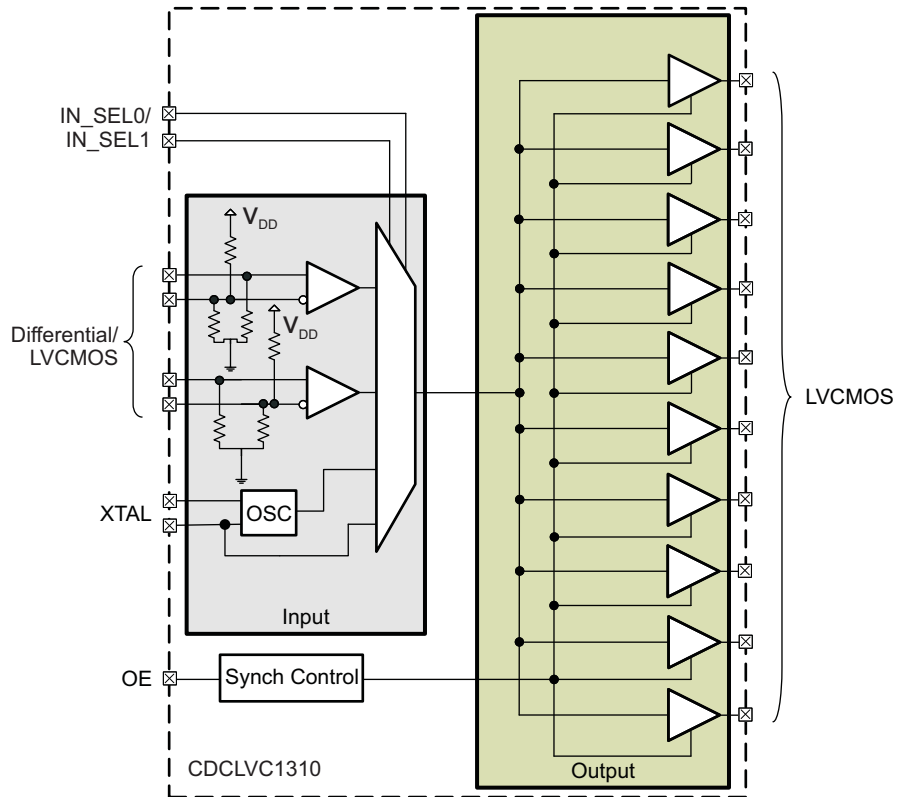
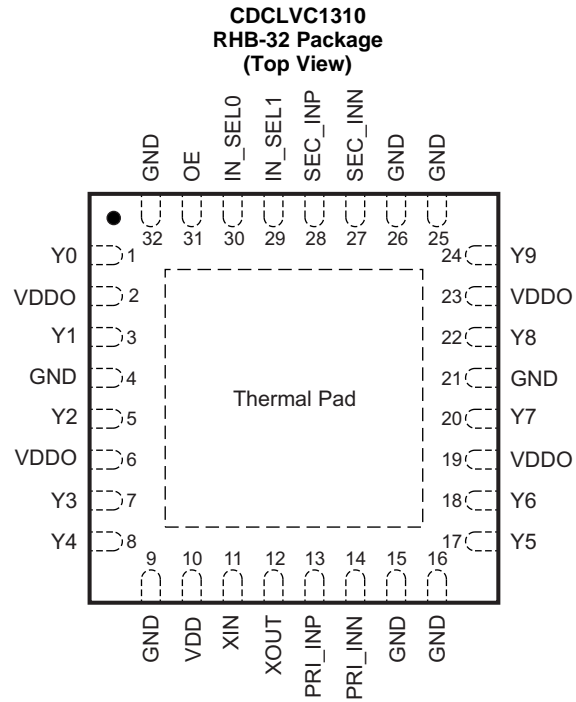


Figure 1. High-Level Block Diagram of CDCLVC1310

PINOUT DIAGRAM



P0048-18

PIN FUNCTIONS

PIN		I/O	TYPE	DESCRIPTION
NAME	NO(s)			
GND	4, 9, 15, 16, 21, 25, 26, 32	PWR	Analog	Power-supply ground
IN_SELO, IN_SEL1	30, 29	I	Digital	Input-clock selection (pulldown of 150 kΩ)
OE	31	I	Digital	LVC MOS output enable (pulldown of 150 kΩ)
PRI_INN	14	I	Analog	Inverting differential primary reference input, internally biased to V _{dd} / 2 (pullup or pulldown of 150 kΩ)
PRI_INP	13	I	Analog	Non-inverting differential or single-ended primary reference input (pulldown of 150 kΩ)
SEC_INN	27	I	Analog	Inverting differential secondary reference input, internally biased to V _{dd} / 2 (pullup or pulldown of 150 kΩ)
SEC_INP	28	I	Analog	Non-inverting differential or single-ended secondary reference input (pulldown of 150 kΩ)
VDD	10	PWR	Analog	Power-supply pins
VDDO	2, 6, 19, 23	PWR	Analog	I/O power-supply pins
XIN	11	I	Analog	Crystal-oscillator input or XTAL bypass mode
XOUT	12	I	Analog	Crystal-oscillator output
Y0	1	O	Analog	LVC MOS output 0
Y1	3	O	Analog	LVC MOS output 1
Y2	5	O	Analog	LVC MOS output 2
Y3	7	O	Analog	LVC MOS output 3
Y4	8	O	Analog	LVC MOS output 4
Y5	17	O	Analog	LVC MOS output 5
Y6	18	O	Analog	LVC MOS output 6
Y7	20	O	Analog	LVC MOS output 7
Y8	22	O	Analog	LVC MOS output 8
Y9	24	O	Analog	LVC MOS output 9

Table 1. Input Selection

IN_SEL1	IN_SELO	INPUT CHOSEN
0	0	PRI_IN
0	1	SEC_IN
1	0	XTAL or overdrive ⁽¹⁾
1	1	XTAL bypass ⁽²⁾

- (1) This mode is for XTAL input or overdrive of XTAL oscillator with LVC MOS input. For characteristics; see [LVC MOS OUTPUT CHARACTERISTICS](#).
- (2) This mode is only XTAL bypass. For characteristics, see [LVC MOS OUTPUT CHARACTERISTICS](#).

Table 2. INPUT/OUTPUT OPERATION⁽¹⁾

INPUT STATE	OUTPUT STATE
PRI_INx, SEC_INx open	Logic LOW
PRI_INP, SEC_INP = HIGH, PRI_INN, SEC_INN = LOW	Logic HIGH
PRI_INP, SEC_INP = LOW, PRI_INN, SEC_INN = HIGH	Logic LOW

- (1) Device must have switching edge to obtain output states.

Table 3. OE Function

OE	Yx
0	High-impedance
1	Enabled

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		VALUE	UNIT
VDD, VDDO	Supply-voltage range	–0.5 to 4.6	V
V _{IN}	Input-voltage range	–0.5 to VDD + 0.5	V
V _{OUT}	Output-voltage range	–0.5 to VDDO + 0.5	V
I _{IN}	Input current	±20	V
I _{OUT}	Output current	±50	V
T _{stg}	Storage-temperature range	–65 to 150	°C
T _J	Junction temperature	125	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDDO	Output supply voltage	3.135	3.3	3.465	V
		2.375	2.5	2.625	
		1.6	1.8	2	
		1.35	1.5	1.65	
VDD	Core supply voltage	3.135	3.3	3.465	V
		2.375	2.5	2.625	
I _{OH}	High-level output current, LVCMOS			–24	mA
I _{OL}	Low-level output current, LVCMOS			24	mA
T _A	Ambient temperature	–40		85	°C

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾		CDCLVC1310	
		RHB	
		32 PINS	
			UNIT
θ_{JA}	Junction-to-ambient thermal resistance ⁽²⁾	41.7	°C/W
θ_{JcTop}	Junction-to-case (top) thermal resistance ⁽³⁾	34.1	°C/W
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	14.4	°C/W
ψ_{JT}	Junction-to-top characterization parameter ⁽⁵⁾	0.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter ⁽⁶⁾	14.4	°C/W
θ_{JcBot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	6.2	°C/W

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ_{JB} , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

INPUT CHARACTERISTICS

over recommended ranges of supply voltage ($V_{DD0} \leq V_{DD}$), load and ambient temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC Characteristic (OE, IN_SEL0, IN_SEL1, PRI_IN, SEC_IN)						
I_{IH}	Input high current	$V_{DD} = 3.465 \text{ V}$, $V_{IH} = 3.465 \text{ V}$			40	μA
I_{IL}	Input low current	$V_{DD} = 3.465 \text{ V}$, $V_{IL} = 0 \text{ V}$			-40	μA
$\Delta V/\Delta T$	Input edge rate	20%–80%		2		V/ns
$R_{Pullup/down}$	Pullup or pulldown resistance			150		k Ω
C_{IN}	Input capacitance			2		pF
Single-Ended DC Characteristic (PRI_INP, SEC_INP)⁽¹⁾						
V_{IH}	Input high voltage	$V_{DD} = 3.3 \text{ V} \pm 5\%$	2		$V_{DD} + 0.3$	V
		$V_{DD} = 2.5 \text{ V} \pm 5\%$	1.6		$V_{DD} + 0.3$	
V_{IL}	Input low voltage	$V_{DD} = 3.3 \text{ V} \pm 5\%$	-0.3		1.3	V
		$V_{DD} = 2.5 \text{ V} \pm 5\%$	-0.3		0.9	
Single-Ended DC Characteristic (OE, IN_SEL0, IN_SEL1)						
V_{IH}	Input high voltage		$0.7 \times V_{DD}$			V
V_{IL}	Input low voltage				$0.3 \times V_{DD}$	V
Differential DC Characteristic (PRI_IN, SEC_IN)						
$V_{I,DIFF}$	Differential input voltage swing ⁽²⁾		0.15		1.3	V
V_{ICM}	Input common-mode voltage ⁽³⁾		0.5		$V_{DD} - 0.85$	V
AC Characteristic (PRI_IN, SEC_IN)						
f_{IN}	Input frequency		DC		200	MHz
idc	Input duty cycle		40%		60%	

- (1) PRI/SEC_INN biased to $V_{DD} / 2$
- (2) V_{IL} should not be less than -0.3 V
- (3) Input common-mode voltage is defined as V_{IH} (see [Figure 19](#)).

CRYSTAL CHARACTERISTICS

over recommended ranges of supply voltage, load and ambient temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Equivalent series resistance (ESR)			50		Ω
Maximum shunt capacitance			7		pF
Drive level			100		μ W

CRYSTAL OSCILLATOR CHARACTERISTICS

over recommended ranges of supply voltage, load and ambient temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Mode of oscillation		Fundamental			
Frequency		8		50	MHz
Frequency in overdrive mode ⁽¹⁾				50	MHz
Frequency in bypass mode ⁽²⁾				50	MHz
On-chip load capacitance			12		pF

(1) Input signal swing (max) = 2 V; input signal t_r (max) = 10 ns; t_f (max) = 10 ns; functional, but device may not meet ac parameters.

(2) Input signal swing (max) = V_{DD} ; input signal t_r (max) = 10 ns; t_f (max) = 10 ns; functional, but device may not meet ac parameters.

LVC MOS OUTPUT CHARACTERISTICS

over recommended ranges of supply voltage ($V_{DDO} \leq V_{DD}$), load (50Ω to $V_{DDO}/2$), and ambient temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{OUT}				200	MHz
V_{OH} Output high voltage	$V_{DDO} = 3.135 \text{ V to } 3.465 \text{ V}$	0.8 * V_{DDO}			V
	$V_{DDO} = 2.375 \text{ V to } 2.625 \text{ V}$	0.8 * V_{DDO}			
	$V_{DDO} = 1.6 \text{ V to } 2 \text{ V}$	0.7 * V_{DDO}			
	$V_{DDO} = 1.35 \text{ V to } 1.65 \text{ V}$	0.7 * V_{DDO}			
V_{OL} Output low voltage	$V_{DDO} = 3.135 \text{ V to } 3.465 \text{ V}$			0.2 * V_{DDO}	V
	$V_{DDO} = 2.375 \text{ V to } 2.625 \text{ V}$			0.2 * V_{DDO}	
	$V_{DDO} = 1.6 \text{ V to } 2 \text{ V}$			0.3 * V_{DDO}	
	$V_{DDO} = 1.35 \text{ V to } 1.65 \text{ V}$			0.3 * V_{DDO}	
R_{OUT} Output impedance	$V_{DDO} = 3.3 \text{ V}$		15		Ω
	$V_{DDO} = 2.5 \text{ V}$		20		
	$V_{DDO} = 1.8 \text{ V}$		25		
	$V_{DDO} = 1.5 \text{ V}$		30		
$t_{SLEW-RATE}$ Output slew rate, rising and falling	$V_{DDO}=3.3\text{V} \pm 5\%$, 20% to 80%	5.6	7.3	9.0	V/ns
	$V_{DDO}=2.5\text{V} \pm 5\%$, 20% to 80%	3.9	4.8	5.4	
	$V_{DDO}=1.8\text{V} \pm 200\text{mV}$, 20% to 80%	1.6	2.1	2.5	
	$V_{DDO}=1.5\text{V} \pm 150\text{mV}$, 20% to 80%	0.9	1.2	1.4	
t_{SK} Output skew			30	50	ps
$t_{SK,PP}$ Part-to-part skew ⁽¹⁾				2	ns

(1) Calculation for part-to-part skew is the difference between the fastest and the slowest t_{pd} across multiple devices.

LVC MOS OUTPUT CHARACTERISTICS (continued)

over recommended ranges of supply voltage ($V_{DDO} \leq V_{DD}$), load (50Ω to $V_{DDO}/2$), and ambient temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{DELAY}	Output frequency	VDD = 3.3 V \pm 5%, VDDO = 1.35 V to VDD	1.5	1.95	4.0	ns
		VDD = 2.5 V \pm 5%, VDDO = 1.35 V to VDD	1.8	2.4	4.4	
t_{RJIT}	System-level additive jitter ⁽²⁾	Single-ended input, VDD = 3.3 V, VDDO = 3.3 V		25		f_s , RMS
		Single-ended input, VDD = 2.5 V or 3.3 V, VDDO = 1.5 V, 1.8 V, or 2.5 V, $f_{\text{IN/OUT}} = 125$ MHz		30		
		Differential input, VDD = 3.3 V, VDDO = 3.3 V		30		
		Differential input, VDD = 2.5 V or 3.3 V, VDDO = 1.5 V, 1.8 V, or 2.5 V, $f_{\text{IN/OUT}} = 125$ MHz		30		
NF	Noise floor	10-kHz offset ⁽³⁾		-145		dBc/Hz
		100-kHz offset ⁽³⁾		-156		
		1-MHz offset ⁽³⁾		-163		
		10-MHz offset ⁽³⁾		-164		
		20-MHz offset ⁽³⁾		-164		
		10-kHz offset ⁽⁴⁾		-145		
		100-kHz offset ⁽⁴⁾		-155		
		1-MHz offset ⁽⁴⁾		-160		
		10-MHz offset ⁽⁴⁾		-161		
20-MHz offset ⁽⁴⁾		-162				
odc	Output duty cycle	$f_{\text{IN/OUT}} = 125$ MHz, $\text{idc} = 50\%$ ⁽⁵⁾	45%		55%	
t_{EN}	Output enable or disable time				2	Cycle
$\text{MUX}_{\text{ISOLATION}}$	MUX isolation ⁽⁶⁾	125 MHz	55			dB

(2) Integration range: 12 kHz–20 MHz; input source see the [System-Level Additive-Jitter Measurement](#) section

(3) Single-ended input, $f_{\text{IN/OUT}} = 125$ MHz, VDD = VDDO = 3.3 V

(4) Differential input, $f_{\text{IN/OUT}} = 125$ MHz, VDD = VDDO = 3.3 V

(5) Stable V_{IH} , V_{IL} , and V_{CM}

(6) See [Figure 18](#).

PHASE NOISE WITH XTAL⁽¹⁾ SELECTED

VDD = VDDO = 2.5 V or 3.3 V, $f_{XTAL} = 25$ MHz, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Jrms	RMS phase jitter	IB = 12 kHz to 5 MHz, VDD = VDDO = 3.3 V		80		fs rms
		IB = 12 kHz to 5 MHz, VDD = VDDO = 2.5 V		115		
PN	Phase noise (see Figure 15)	$f_{offset} = 100$ Hz, VDD = VDDO = 3.3 V		-92		dBc/Hz
		$f_{offset} = 1$ kHz, VDD = VDDO = 3.3 V		-137		
		$f_{offset} = 10$ kHz, VDD = VDDO = 3.3 V		-163		
		$f_{offset} = 100$ kHz, VDD = VDDO = 3.3 V		-168		
		$f_{offset} = 1$ MHz, VDD = VDDO = 3.3 V		-168		
		$f_{offset} = 5$ MHz, VDD = VDDO = 3.3 V		-169		
		$f_{offset} = 100$ Hz, VDD = VDDO = 2.5 V		-91		
		$f_{offset} = 1$ kHz, VDD = VDDO = 2.5 V		-136		
		$f_{offset} = 10$ kHz, VDD = VDDO = 2.5 V		-159		
		$f_{offset} = 100$ kHz, VDD = VDDO = 2.5 V		-164		
		$f_{offset} = 1$ MHz, VDD = VDDO = 2.5 V		-165		
$f_{offset} = 5$ MHz, VDD = VDDO = 2.5 V		-165				

(1) Crystal specification: $C_L = 18$ pF; ESR = 35 Ω (max); $C_0 = 7$ pF; drive level = 100 μW (max)

DEVICE CURRENT CONSUMPTION

over recommended ranges of supply voltage, load and ambient temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OVERALL PARAMETERS FOR ALL VERSIONS						
I _{DD}	Static device current ⁽¹⁾	OE = 0 V or V _{DD} ; Ref. input (PRI/SEC) = 0 V or V _{DD} ; I _O = 0 mA; V _{DD} / V _{DDO} = 3.3 V		14		mA
		OE = 0 V or V _{DD} ; Ref. input (PRI/SEC) = 0 V or V _{DD} ; I _O = 0 mA; V _{DD} / V _{DDO} = 2.5 V		8		
I _{DD,XTAL}	Device current with XTAL input ⁽¹⁾			20		mA
C _{PD}	Power dissipation capacitance per output ⁽²⁾	VDDO = 3.465 V; f = 100 MHz			8.8	pF
		VDDO = 2.625 V; f = 100 MHz			7.7	
		VDDO = 2 V; f = 100 MHz			7.3	
		VDDO = 1.65 V; f = 100 MHz			6.9	

(1) I_{DD} and I_{DD,XTAL} is the current through V_{DD}; outputs enabled or in the high-impedance state; no load.

(2) This is the formula for the power dissipation calculation (see the [Power Considerations](#) section)

$$I_{DD,Total} = I_{DD} + I_{DD,Cload} + I_{DD,dyn} \text{ [mA]}$$

$$I_{DD,dyn} = C_{PD} \times V_{DDO} \times f \times n \text{ [mA]}$$

$$I_{DD,Cload} = C_{load} \times V_{DDO} \times f \times n \text{ [mA]}$$

$$n = \text{Number of switching output pins}$$

TEST CONFIGURATIONS

Figure 2 through Figure 8 illustrate how to set up the device for a variety of test configurations.

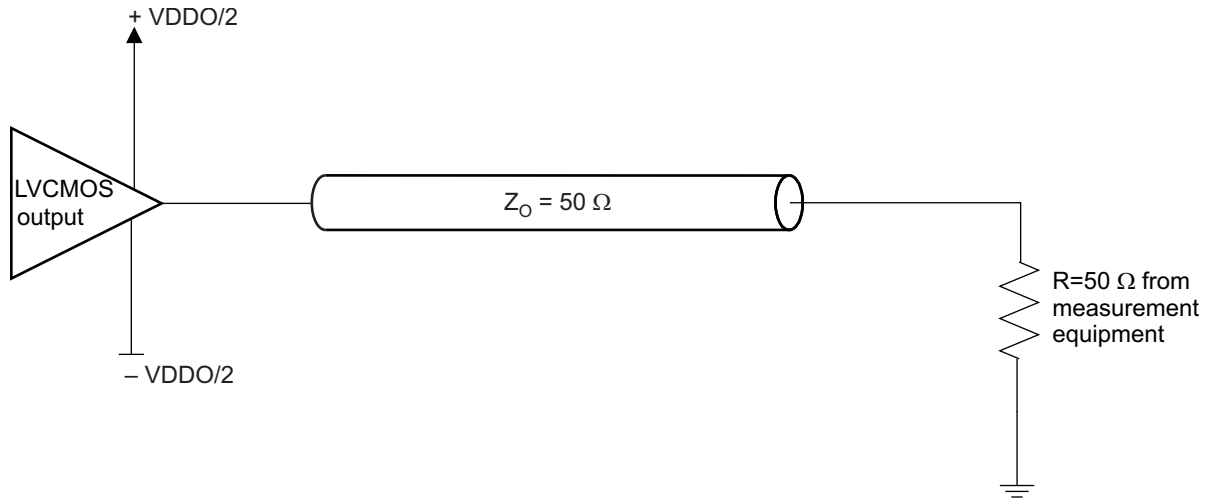


Figure 2. LVC MOS Output DC Configuration; Test Load Circuit

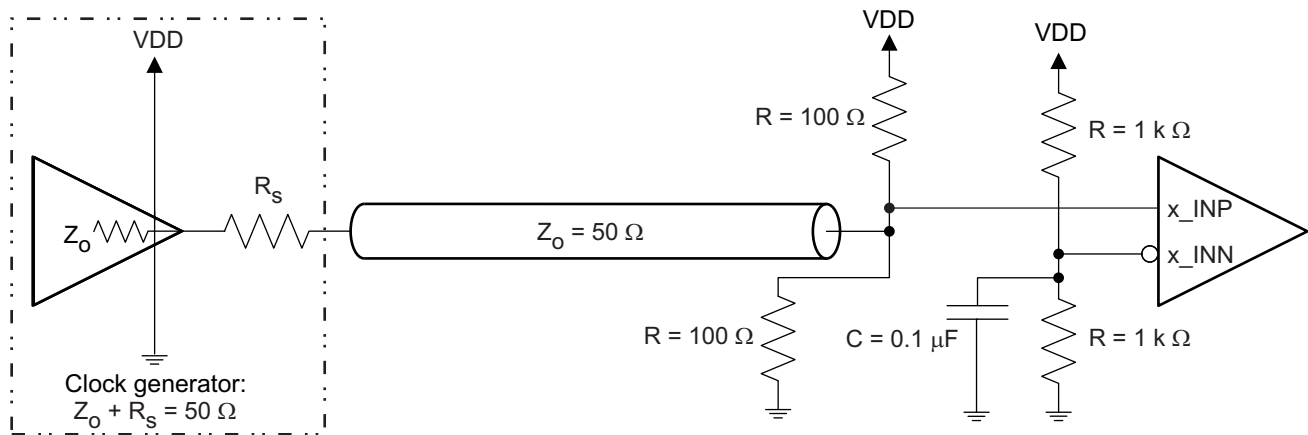


Figure 3. LVC MOS Input DC Configuration During Device Test

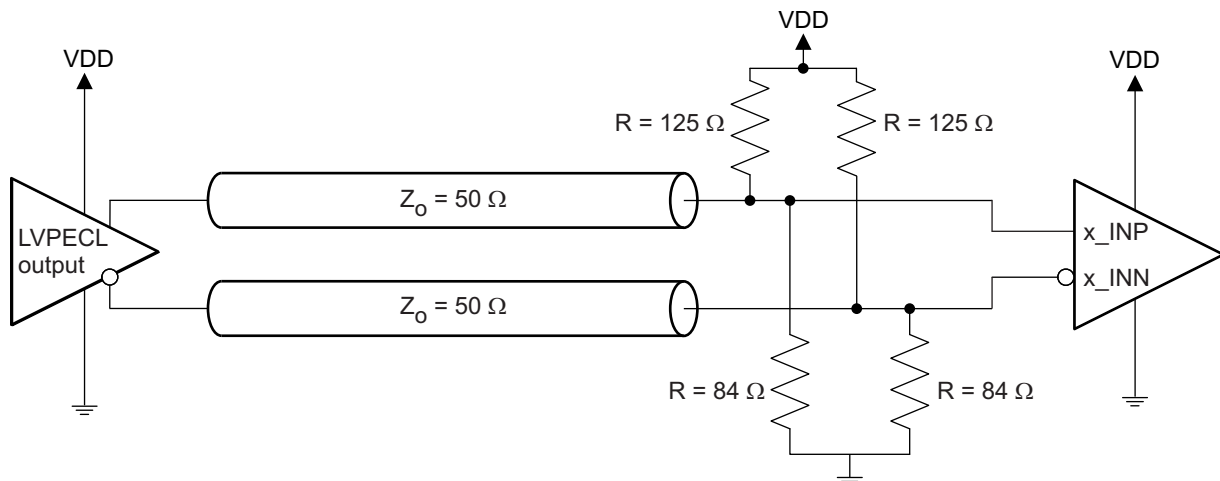


Figure 4. LVPECL Input Configuration During Device Test

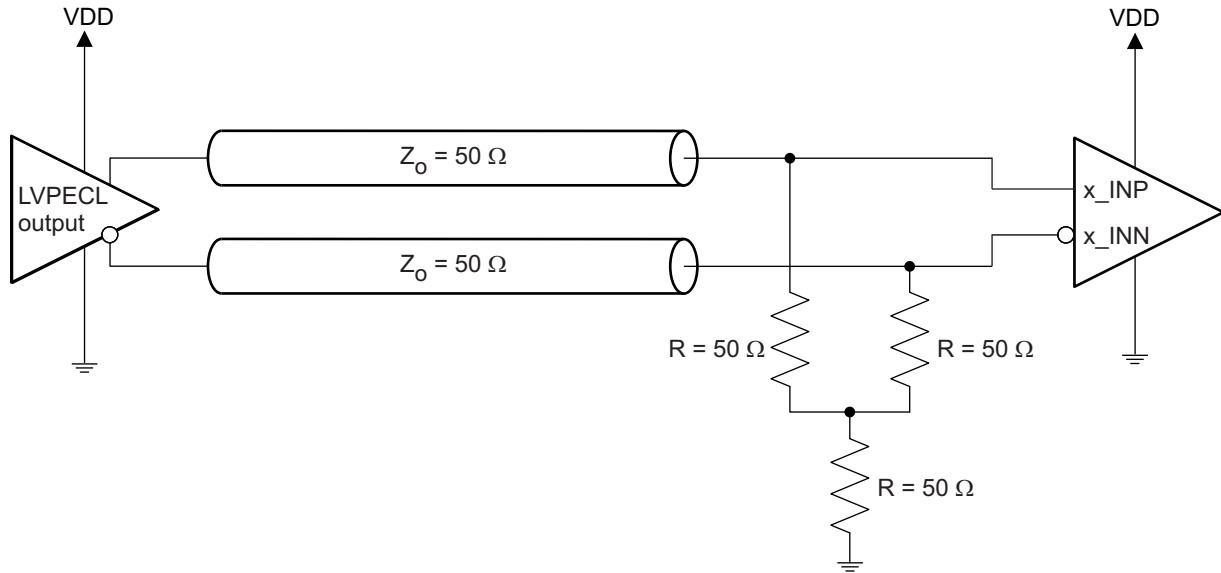


Figure 5. LVPECL Input Configuration During Device Test

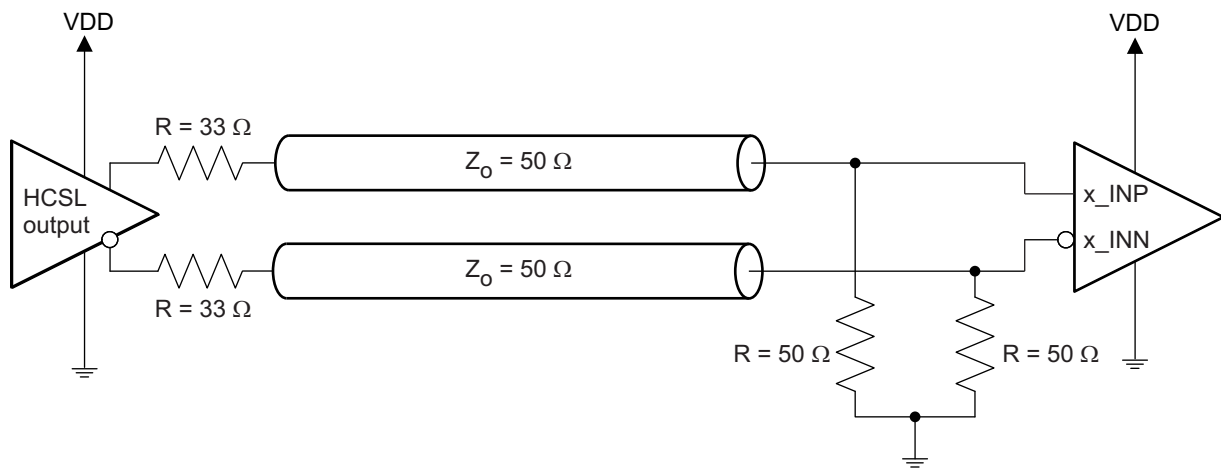


Figure 6. HCSL Input Configuration During Device Test

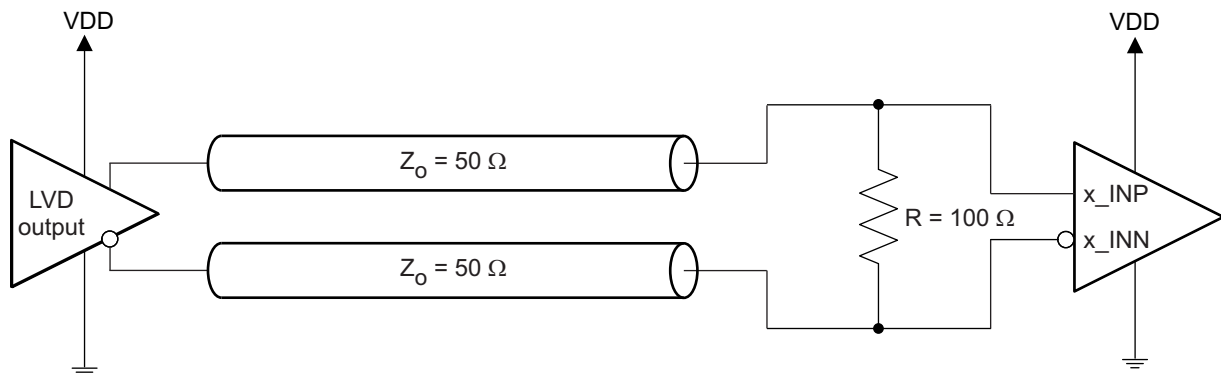


Figure 7. LVDS Input Configuration During Device Test

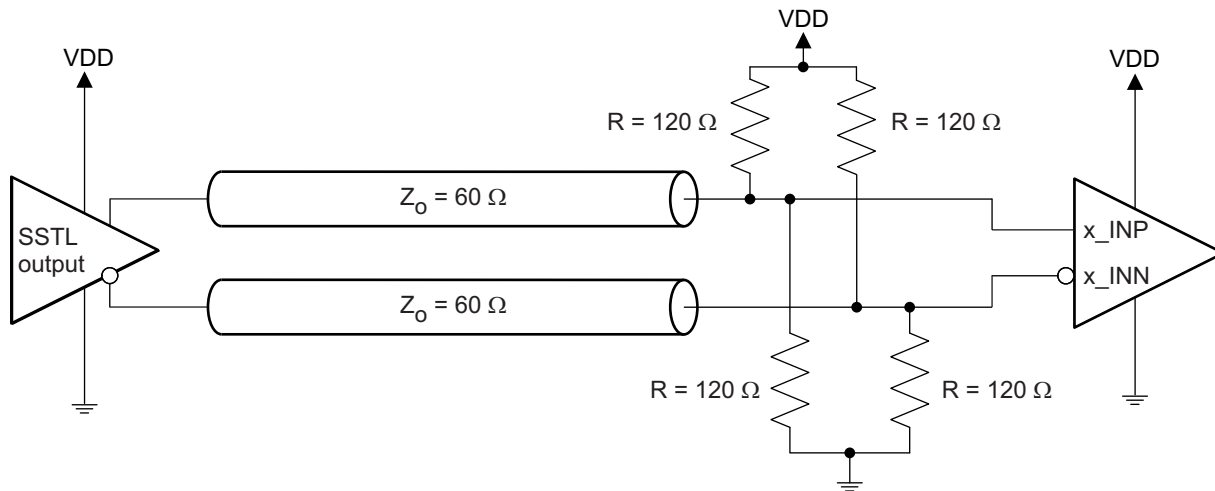


Figure 8. SSSL Input Configuration During Device Test

APPLICATION INFORMATION

Typical Application Load

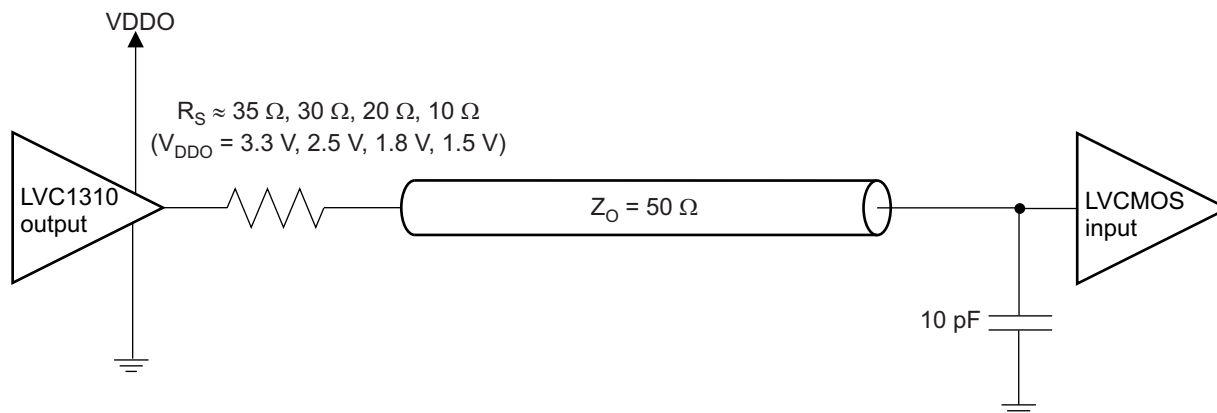


Figure 9. LVC1310 Output DC Configuration: Typical Application Load

Parameter Measurement Information

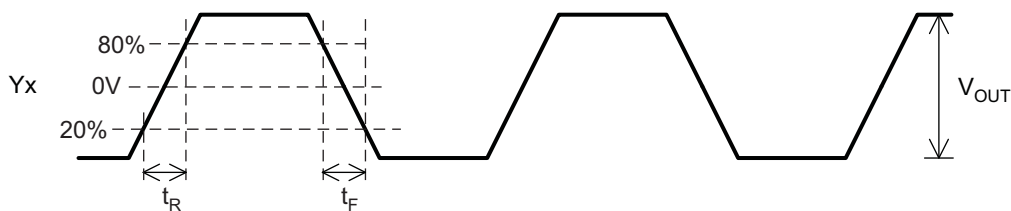


Figure 10. LVC1310 Output Voltage, and Rise and Fall Times

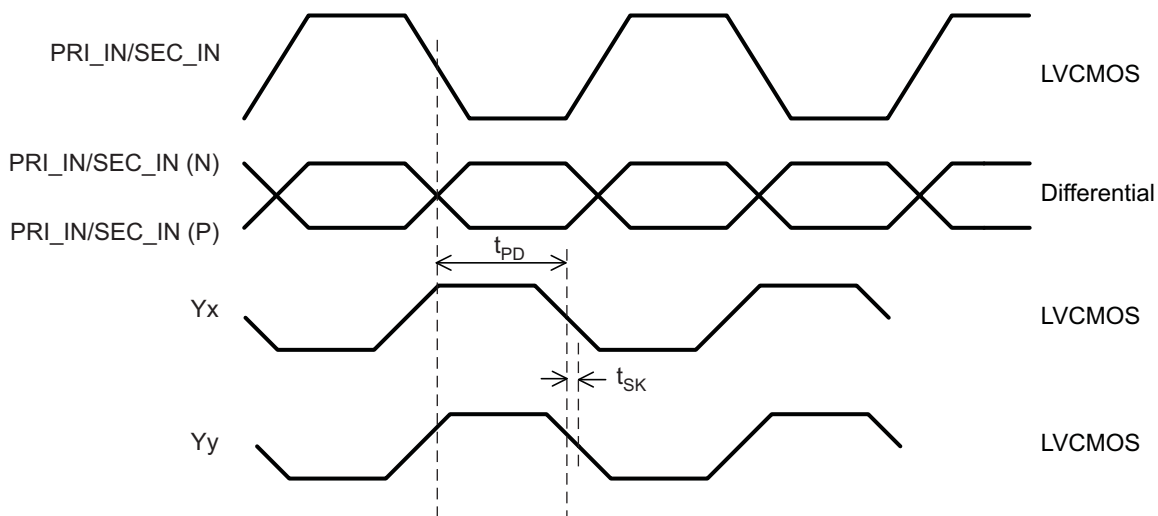


Figure 11. Differential and Single-Ended Output Skew and Propagation Delay

Crystal Oscillator Input

The crystal oscillator circuit is characterized with 18-pF parallel-resonant crystals. Choices of C1 and C2 were to minimize the ppm error. Optional resistor $R_{OPTIONAL}$ limits the drive level of the oscillator circuit.

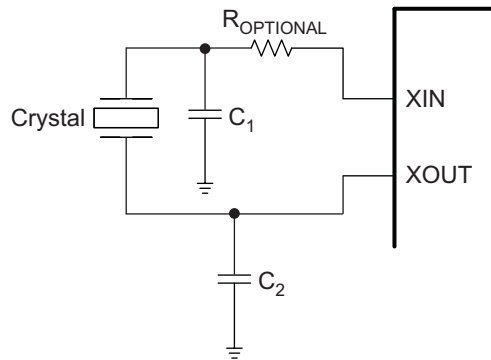


Figure 12. Crystal Reference Input

The input XIN can accept single-ended LVCMOS signals in two configurations. It is possible to overdrive the oscillator stage or to use a pure LVCMOS input (see Table 1). If overdriving the oscillator stage, it is necessary to ac-couple the input with a capacitor (see Figure 13). Otherwise, if selecting the bypass, there is no requirement for a coupling capacitor. Additional measurements and information about crystal oscillator input and limiting the drive level are available in the applications report *Crystal Oscillator Performance of the CDCLVC1310 (SCAA119)*.

NOTE

If using the overdrive or bypass mode, the device is functional, but may not meet its ac parameters.

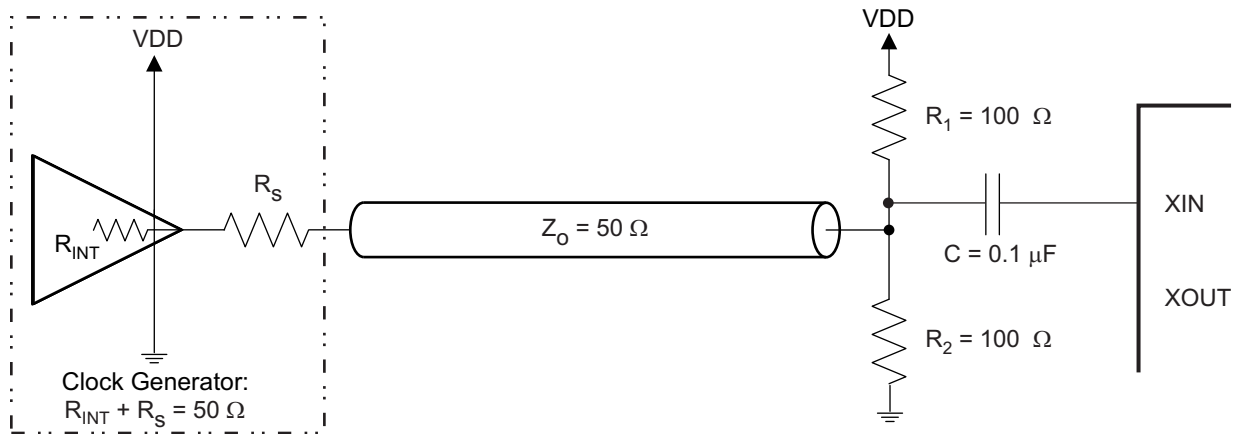


Figure 13. Single-Ended Crystal Input

Phase-Noise Performance

The CDCLVC1310 provides ultralow phase-noise outputs (noise floor = -170 dBc/Hz) if it has an attached crystal. Figure 14 shows the phase-noise plot of the CDCLVC1310 with a 25-MHz crystal at $V_{DD} = V_{DDO} = 3.3$ V and room temperature.

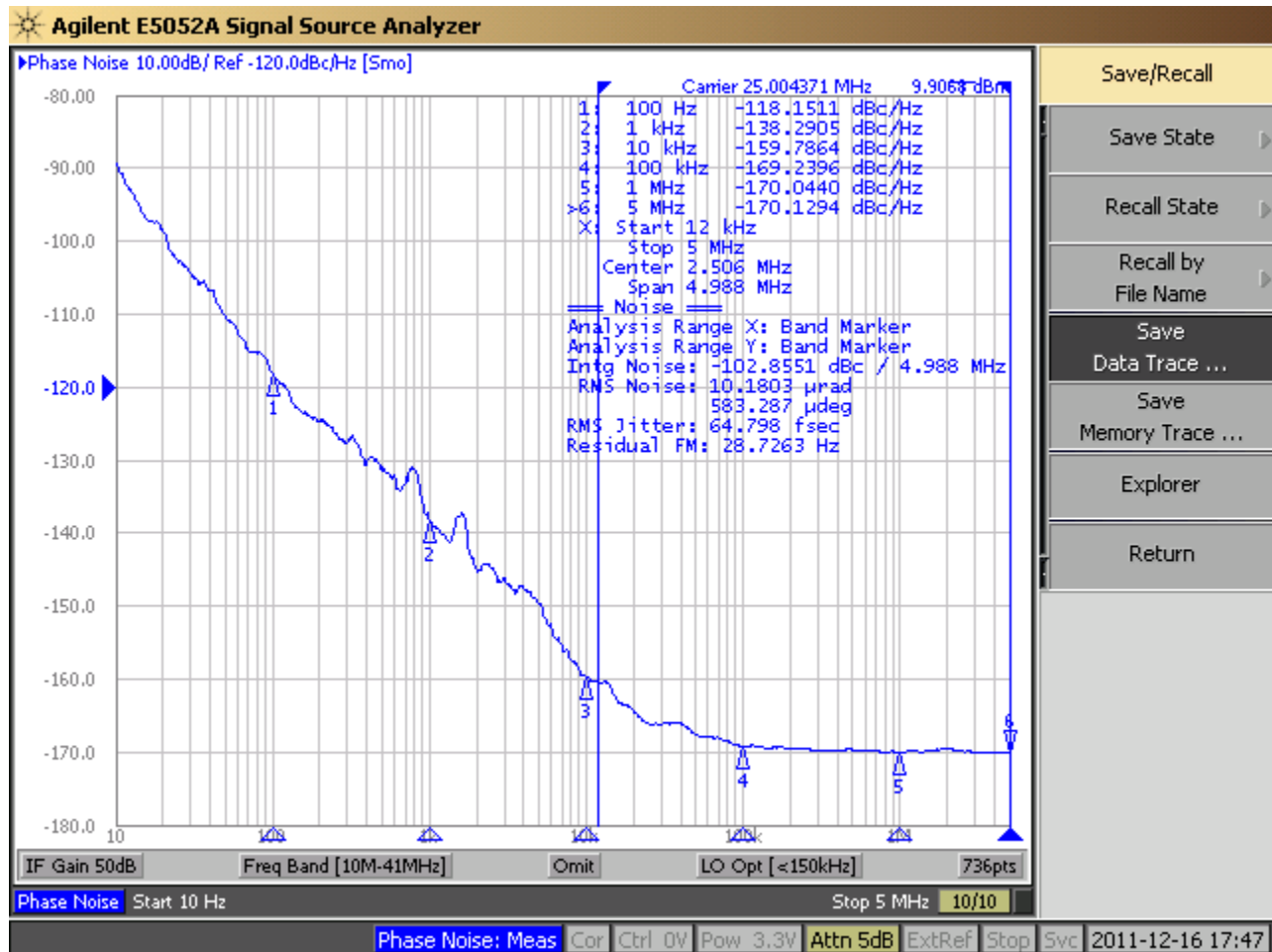


Figure 14. Phase-Noise Profile With 25-MHz Crystal at Nominal Conditions

System-Level Additive-Jitter Measurement

For high-performance devices, limitations of the equipment influence phase-noise measurements. The noise floor of the equipment often exceeds the noise floor of the device. The real noise floor of the device is probably lower (see [LVCMOS Output Characteristics](#)). Phase noise is influenced by the input source and the measurement equipment. Additional measurements and information about system-level additive jitter and noise floor are available in the applications report *Phase Noise Performance of CDCLVC1310 (SCAA115)*.

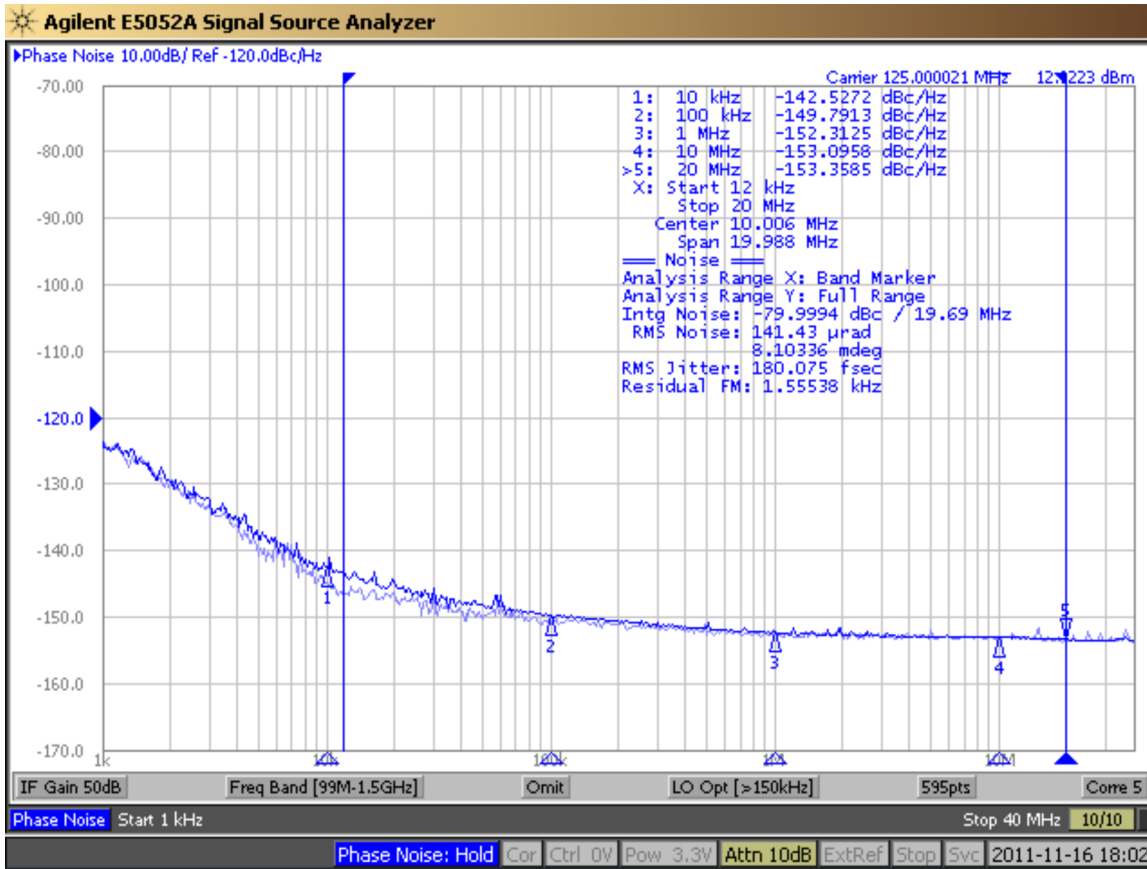


Figure 15. Input Phase Noise (179.4 fs, Light Blue) and Output Phase Noise (180 fs, Dark Blue)

Output Enable

Pulling OE to LOW (t_1), forces the outputs to the high-impedance state after the next falling edge of the input signal (t_2). The outputs remain in the high-impedance state as long as OE is LOW (see Figure 16).

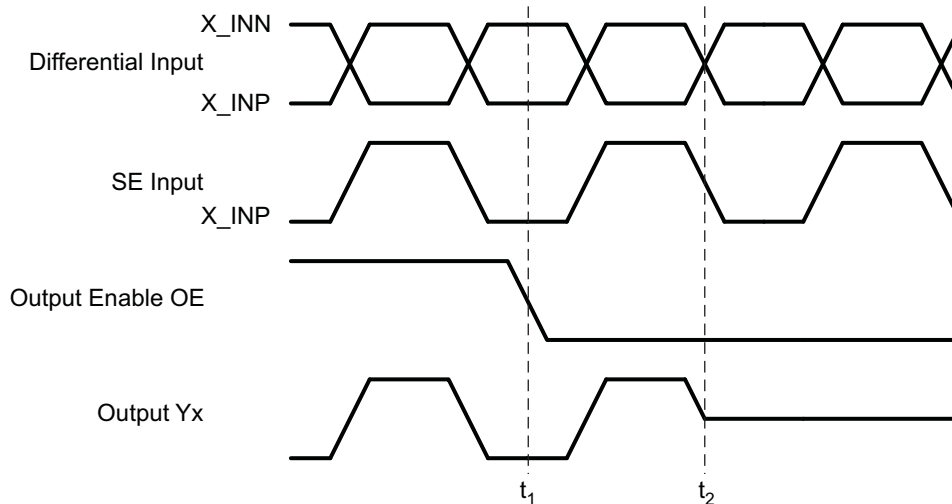


Figure 16. OE: Disable Outputs

If the outputs are in the high-impedance state, pulling OE to HIGH forces all outputs LOW asynchronously (t_3). Within two clock cycles (maximum), the outputs start switching again (t_4), after a falling edge of the input signal (see Figure 17).

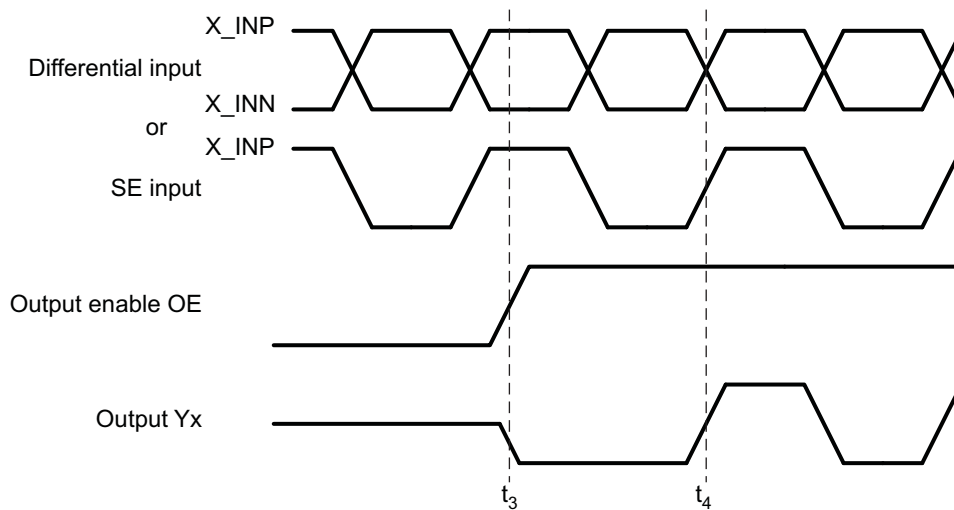


Figure 17. OE: Enable Outputs

If the outputs are in the high-impedance state and the input is static (no clock signal), OE works fully asynchronously. A transition of OE from LOW to HIGH forces the outputs to LOW. A transition from HIGH to LOW does not force to the high-impedance state again. Therefore, a state change requires a falling edge of the input signal (see Figure 16).

MUX Isolation

The definition of MUX isolation is the difference in output amplitude (dB) between an active and a static input signal.

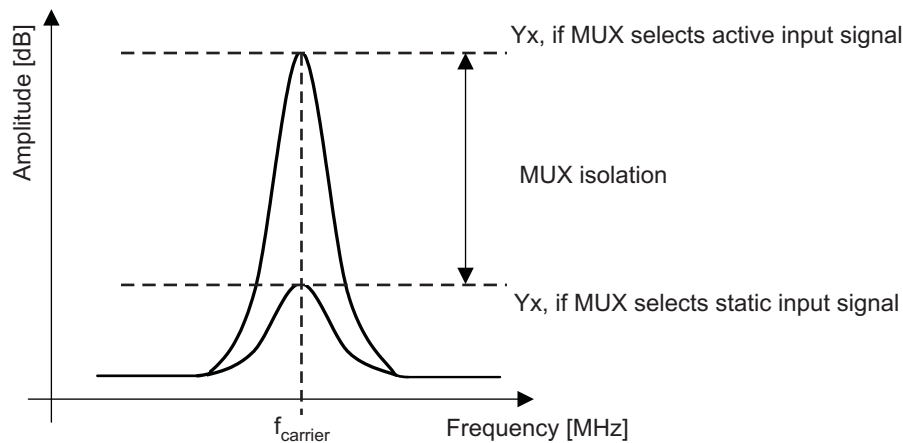
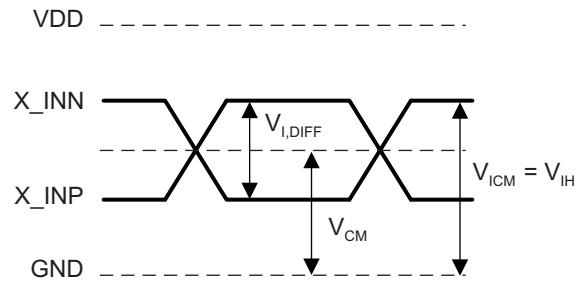


Figure 18. Output Spectrum of an Active and a Static Input Signal

Differential Input Level



NOTE: The calculation for VCM is: $V_{CM} = V_{DD} - V_{ICM} - V_{I,DIFF}/2$

Figure 19. Differential Input Level

Power Considerations

The following power consideration refers to the device-consumed power consumption only. The device power consumption is the sum of static power and dynamic power. The dynamic power usage consists of two components:

- Power used by the device as it switches states
- Power required to charge any output load

The output load can be capacitive-only or capacitive and resistive. Use the following formula to calculate the power consumption of the device:

$$P_{Dev} = P_{stat} + P_{dyn} + P_{Cload} \text{ (see Figure 20 and Figure 21)}$$

$$P_{stat} = I_{DD} \times V_{DD}$$

$$P_{dyn} + P_{Cload} = (I_{DD,dyn} + I_{DD,Cload}) \times V_{DDO}$$

where:

$$I_{DD,dyn} = C_{PD} \times V_{DDO} \times f \times n \text{ [mA]} \text{ (see Figure 22)}$$

$$I_{DD,Cload} = C_{load} \times V_{DDO} \times f \times n \text{ [mA]}$$

Example for power consumption of the CDCLVC1310: 10 outputs are switching, $f = 100 \text{ MHz}$, $V_{DD} = V_{DDO} = 3.3 \text{ V}$ and assuming $C_{load} = 2 \text{ pF}$ per output:

$$P_{Dev} = 46.2 \text{ mW} + 117.5 \text{ mW} = 163.7 \text{ mW}$$

$$P_{stat} = 14 \text{ mA} \times 3.3 \text{ V} = 46.2 \text{ mW}$$

$$P_{dyn} + P_{Cload} = (29 \text{ mA} + 6.6 \text{ mA}) \times 3.3 \text{ V} = 117.5 \text{ mW}$$

$$I_{DD,dyn} = 8.8 \text{ pF} \times 3.3 \text{ V} \times 100 \text{ MHz} \times 10 = 29 \text{ mA}$$

$$I_{DD,Cload} = 2 \text{ pF} \times 3.3 \text{ V} \times 100 \text{ MHz} \times 10 = 6.6 \text{ mA}$$

NOTE

For dimensioning the power supply, consider the total power consumption. The total power consumption is the sum of device power consumption and the power consumption of the load.

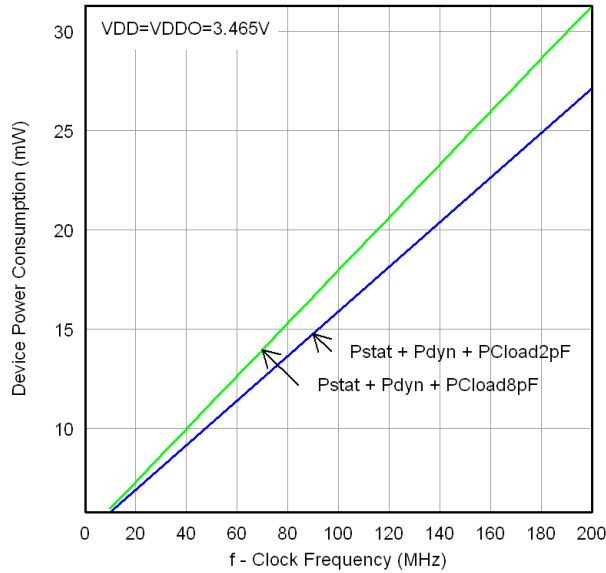


Figure 20. Device Power Consumption versus Clock Frequency (VDD = VDDO = 3.465 V; Load 2 pF, 8 pF; per Output)

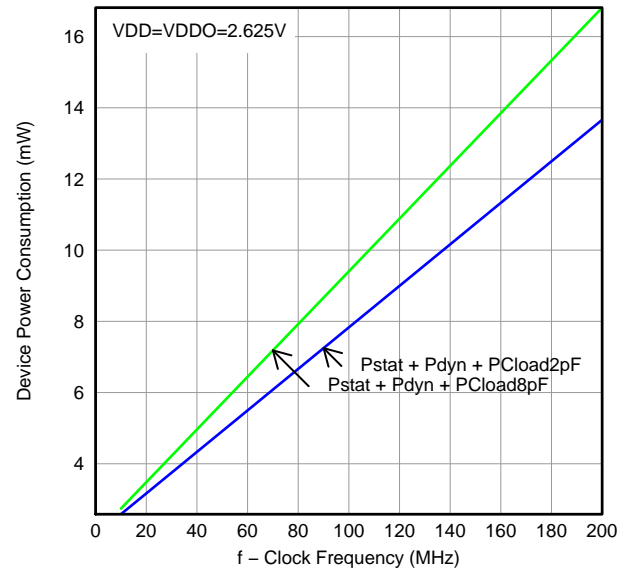


Figure 21. Device Power Consumption versus Clock Frequency (VDD = VDDO = 2.625 V; Load 2 pF, 8 pF; per Output)

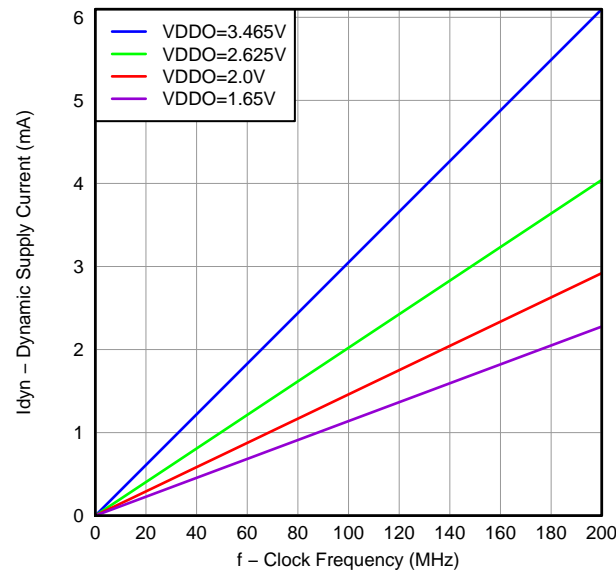


Figure 22. Dynamic Supply Current versus Clock Frequency (per Output)

Thermal Management

Power consumption of the CDCLVC1310 can be high enough to require attention to thermal management. For reliability and performance reasons, limit the die temperature to a maximum of 125°C. That is, as an estimate, T_A (ambient temperature) plus device power consumption times θ_{JA} should not exceed 125°C.

The device package has an exposed pad that provides the primary heat removal path as well as an electrical grounding to the printed circuit board (PCB). To maximize the removal of heat from the package, incorporate a thermal landing pattern including multiple vias to a ground plane on the PCB within the footprint of the package. Solder the exposed pad down to ensure adequate heat conduction out of the package. Figure 23 shows a recommended land and via pattern.

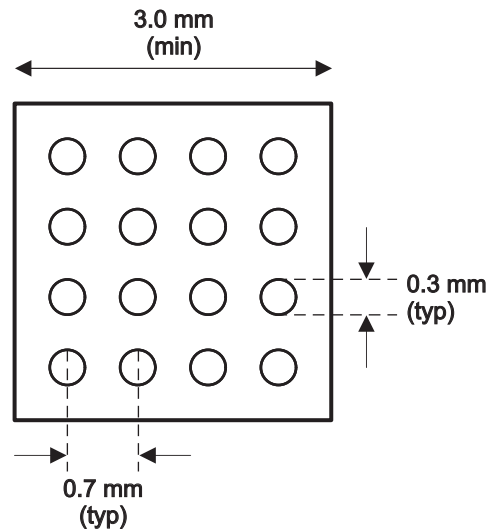


Figure 23. Recommended PCB Layout for CDCLVC1310

Power-Supply Filtering

High-performance clock buffers are sensitive to noise on the power supply, which can dramatically increase the additive jitter of the buffer. Thus, it is essential to reduce noise from the system power supply, especially when jitter or phase noise is very critical to applications.

Use of filter capacitors eliminates the low-frequency noise from power supply, where the bypass capacitors provide the very low-impedance path for high-frequency noise and guard the power-supply system against induced fluctuations. The bypass capacitors also provide instantaneous current surges as required by the device, and should have low ESR. To use the bypass capacitors properly, place them very close to the power supply pins and lay out traces with short loops to minimize inductance. TI recommends to adding as many high-frequency (for example, 0.1- μF) bypass capacitors as there are supply pins in the package. There is a recommendation, but not a requirement, to insert a ferrite bead between the board power supply and the chip power supply to isolate the high-frequency switching noises generated by the clock driver, preventing them from leaking into the board supply. Choosing an appropriate ferrite bead with very low dc resistance is important, because it is imperative to provide adequate isolation between the board supply and the chip supply, and to maintain a voltage at the supply pins that is greater than the minimum voltage required for proper operation.

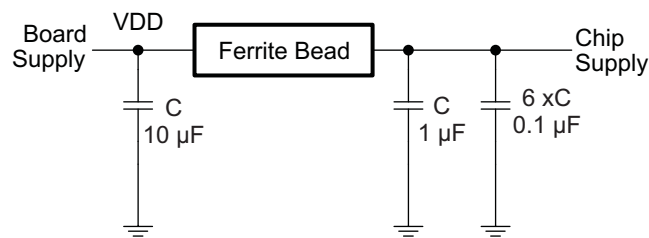


Figure 24. Power-Supply Decoupling

REVISION HISTORY

Changes from Revision D (July 2013) to Revision E	Page
• Changed V_{OH} in LVCMOS OUTPUT CHARACTERISTICS	7
• Changed V_{OL} in LVCMOS OUTPUT CHARACTERISTICS	7
• Changed $t_{SLEW-RATE}$ in LVCMOS OUTPUT CHARACTERISTICS	7
Changes from Revision C (October 2012) to Revision D	Page
• Changed t_{DELAY} in LVCMOS OUTPUT CHARACTERISTICS	8
Changes from Revision B (February 2012) to Revision C	Page
• Changed unit for phase jitter from picosecond to femtosecond	9
• Revised Figure 3	10
• Revised Figure 4	10
• Revised Figure 5	11
• Revised Figure 6	11
• Revised Figure 8	12
• Added reference to application report SCAA119	14

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CDCLVC1310RHBR	Active	Production	VQFN (RHB) 32	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CDCLVC 1310
CDCLVC1310RHBR.B	Active	Production	VQFN (RHB) 32	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CDCLVC 1310
CDCLVC1310RHBRG4.B	Active	Production	VQFN (RHB) 32	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CDCLVC 1310

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCLVC1310RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CDCLVC1310RHBR	VQFN	RHB	32	3000	346.0	346.0	33.0

GENERIC PACKAGE VIEW

RHB 32

VQFN - 1 mm max height

5 x 5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

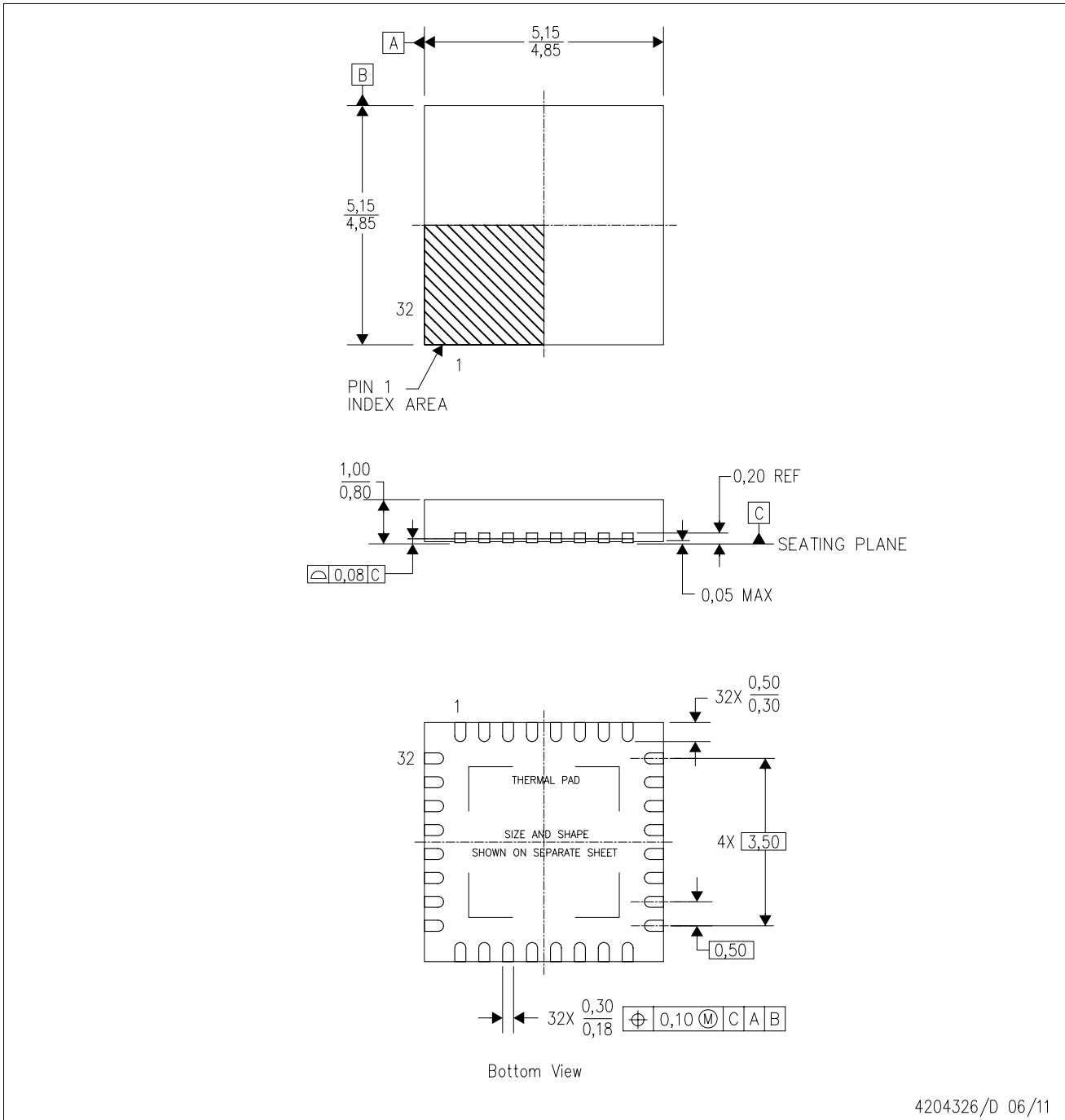


Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4224745/A

RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



4204326/D 06/11

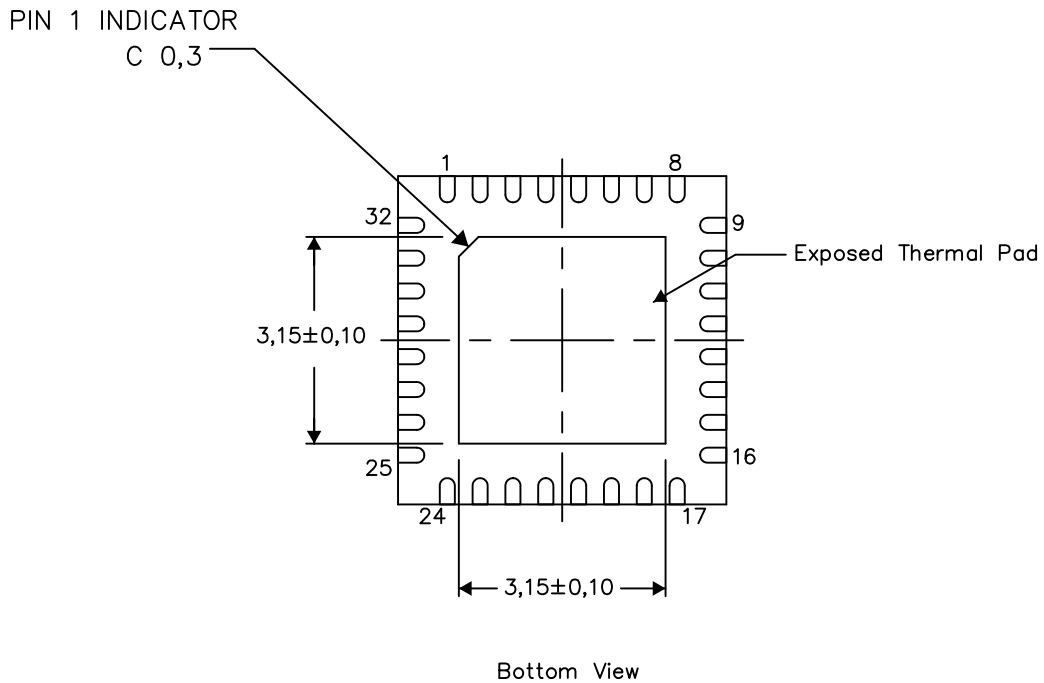
- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - QFN (Quad Flatpack No-Lead) Package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - Falls within JEDEC MO-220.

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



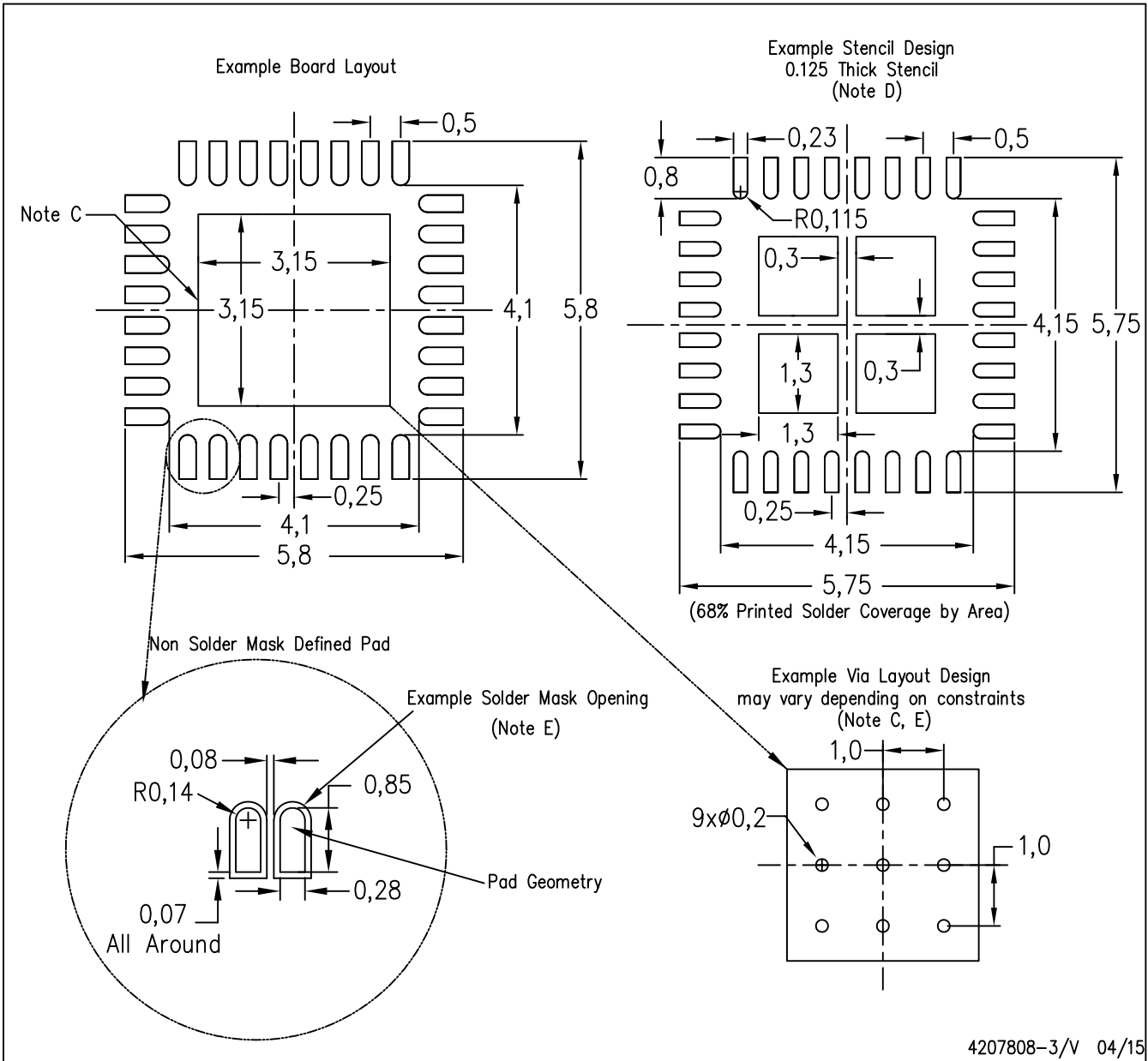
Exposed Thermal Pad Dimensions

4206356-3/AC 05/15

NOTE: A. All linear dimensions are in millimeters

RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



4207808-3/V 04/15

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for any larger diameter vias placed in the thermal pad.

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 [TI 的销售条款](#) 或 [ti.com](#) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
版权所有 © 2025，德州仪器 (TI) 公司